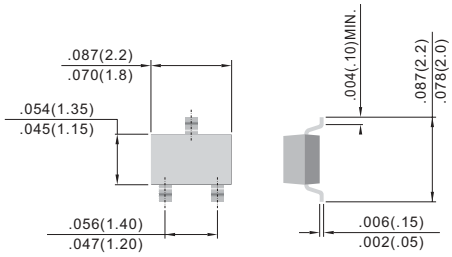
DATA SHEET

MMBT3906W

PNP GENERAL PURPOSE SWITCHING TRANSISTOR

VOLTAGE 40 Volts **POWER** 150 mWatts

SOT-323 Unit: inch (mm)



FEATURES

- PNP epitaxial silicon, planar design
- Collector-emitter voltage VCE = -40V
- Collector current IC = -200mA
- Pb free product are available : 99% Sn above can meet RoHS environment substance directive request

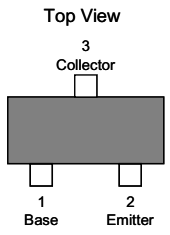
MECHANICAL DATA

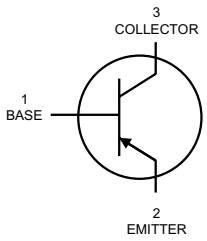
Case: SOT-323, Plastic

Terminals: Solderable per MIL-STD-750, Method 2026

Approx. Weight: 0.0052 gram

Marking: S2A





ABSOLUTE RATINGS

PARAMETER	Symbol	Value	Units
Collector-Emitter Voltage	V_{CEO}	-40	V
Collector-Base Voltage	V_{CBO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Collector Current-Continuous	I_C	-200	mA

THERMAL CHARACTERISTICS

PARAMETER	Symbol	Value	Units
Max Power Dissipation (Note 1)	P_{TOT}	150	mW
Thermal Resistance , Junction to Ambient	$R\theta_{JA}$	833	°C/W
Junction Temperature	T_J	-55 to 150	°C
Storage Temperature	T_{STG}	-55 to 150	°C

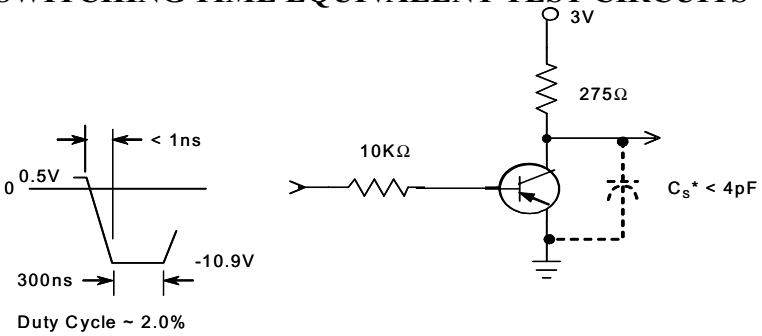
Note 1: Transistor mounted on FR-5 board 1.0 x 0.75 x 0.062 in.

ELECTRICAL CHARACTERISTICS

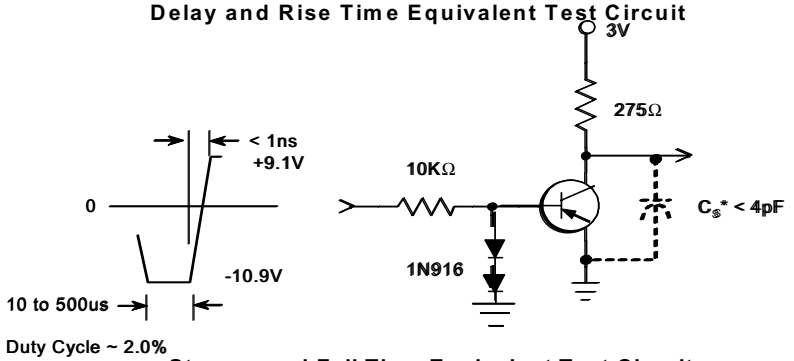
PARAMETER	Symbol	Test Condition	MIN.	TYP.	MAX.	Units
Collector - Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=-1.0mA, I_B=0	-40	-	-	V
Collector - Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=-10uA, I_E=0	-40	-	-	V
Emitter - Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=-10uA, I_C=0	-5.0	-	-	V
Base Cutoff Current	I_{BL}	V_{CE}=-30V, V_{EB}=-3.0V	-	-	-50	nA
Collector Cutoff Current	I_{CEX}	V_{CE}=-30V, V_{EB}=-3.0V	-	-	-50	nA
DC Current Gain (Note 2)	h_{FE}	I_C=-0.1mA, V_{CE}=-1.0V I_C=-1.0mA, V_{CE}=-1.0V I_C=-10mA, V_{CE}=-1.0V I_C=-50mA, V_{CE}=-1.0V I_C=-100mA, V_{CE}=-1.0V	60 80 100 60 30	- - - - -	- - 300 - -	-
Collector - Emitter Saturation Voltage (Note 2)	$V_{CE(SAT)}$	I_C=-10mA, I_B=-1.0mA I_C=-50mA, I_B=-5.0mA	-	-	-0.25 -0.4	V
Base - Emitter Saturation Voltage (Note 2)	$V_{BE(SAT)}$	I_C=-10mA, I_B=-1.0mA I_C=-50mA, I_B=-5.0mA	-0.65 -	- -	-0.85 -0.95	V
Collector - Base Capacitance	C_{CBO}	V_{CB}=-5V, I_E=0, f=1MHz	-	-	4.5	pF
Emitter - Base Capacitance	C_{EBO}	V_{CB}=-0.5V, I_C=0, f=1MHz	-	-	10	pF
Delay Time	td	V_{CC}=-3V, V_{BE}=-0.5V, I_C=-10mA, I_B=-1.0mA	-	-	35	ns
Rise Time	tr	V_{CC}=-3V, V_{BE}=-0.5V, I_C=-10mA, I_B=-1.0mA	-	-	35	ns
Storage Time	ts	V_{CC}=-3V, I_C=-10mA I_{B1}=I_{B2}=-1.0mA	-	-	225	ns
Fall Time	tf	V_{CC}=-3V, I_C=-10mA I_{B1}=I_{B2}=-1.0mA	-	-	75	ns

Note 2: Pulse Test: Pulse Width < 300 us, Duty Cycle < 2.0%.

SWITCHING TIME EQUIVALENT TEST CIRCUITS



Delay and Rise Time Equivalent Test Circuit



Storage and Fall Time Equivalent Test Circuit

ELECTRICAL CHARACTERISTICS CURVE

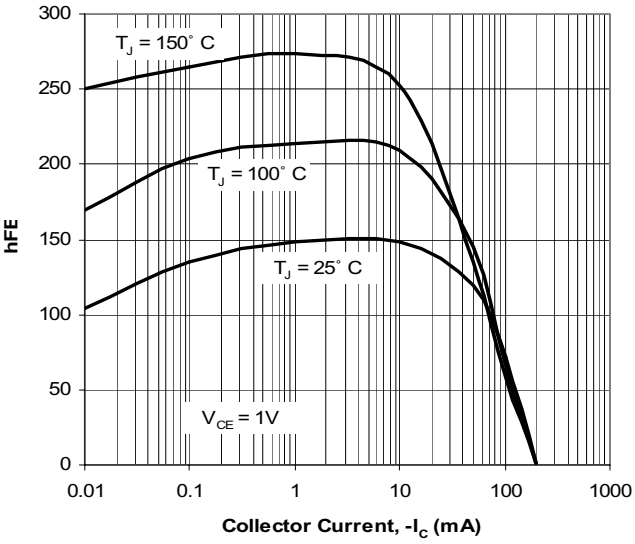


Fig. 1. Typical h_{FE} vs. Collector Current

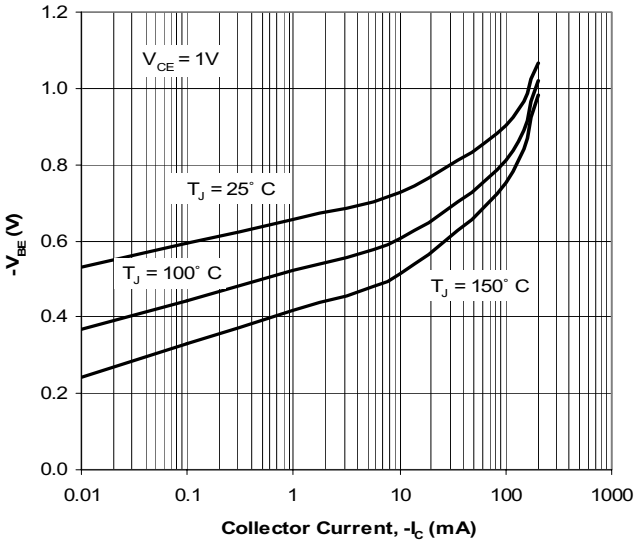


Fig. 2. Typical V_{BE} vs. Collector Current

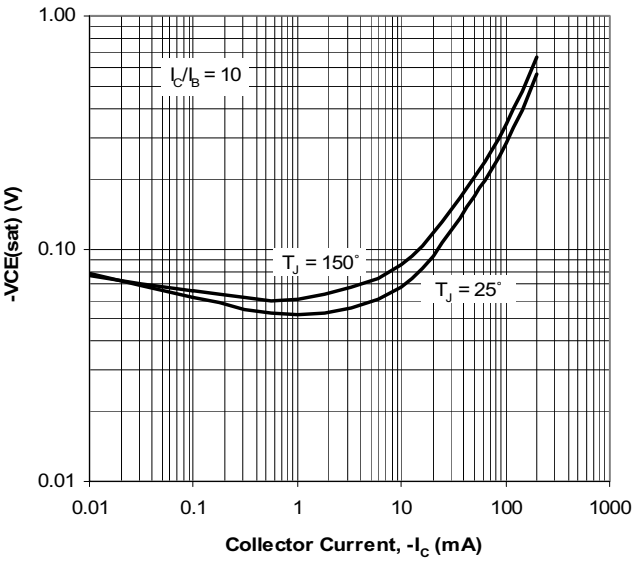


Fig. 3. Typical $V_{CE\ (sat)}$ vs. Collector Current

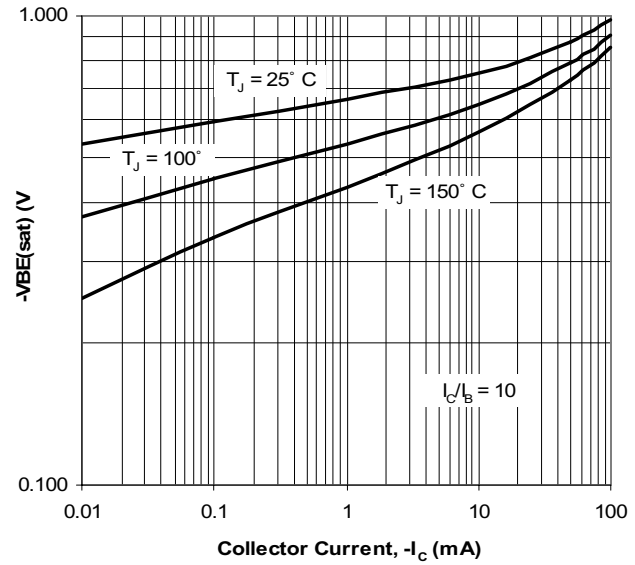


Fig. 4. Typical $V_{BE\ (sat)}$ vs. Collector Current

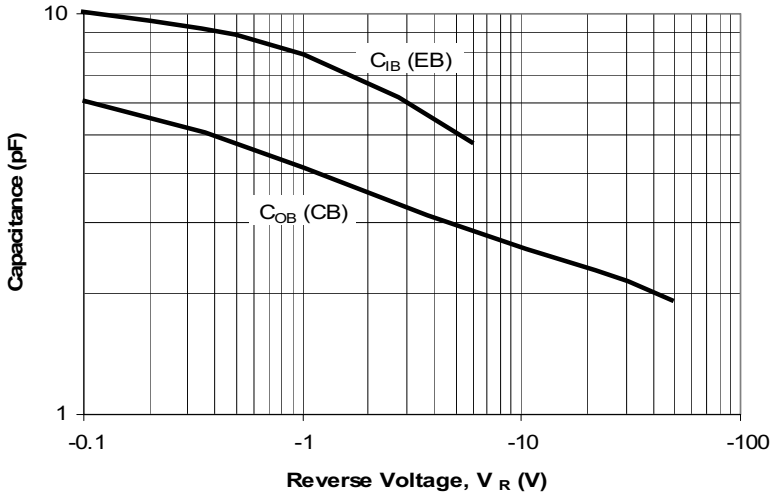
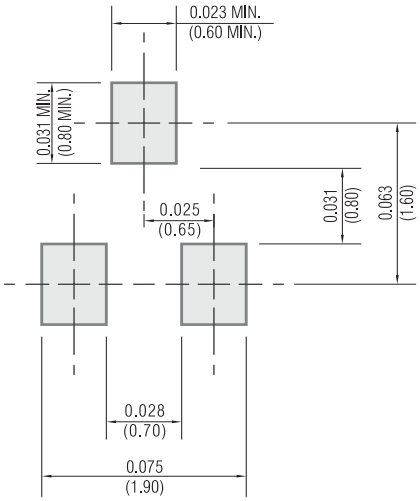


Fig. 5. Typical Capacitances vs. Reverse Voltage

MOUNTING PAD LAYOUT

SOT-323 Unit: inch (mm)



ORDER INFORMATION

- Packing information

  T/R - 10K per 13" plastic Reel

  T/R - 3K per 7" plastic Reel

LEGAL STATEMENT

IMPORTANT NOTICE

This information is intended to unambiguously characterize the product in order to facilitate the customer's evaluation of the device in the application. The information will help the customer's technical experts determine that the device is compatible and interchangeable with similar devices made by other vendors. The information in this data sheet is believed to be reliable and accurate. The specifications and information herein are subject to change without notice. New products and improvements in products and product characterization are constantly in process. Therefore, the factory should be consulted for the most recent information and for any special characteristics not described or specified.